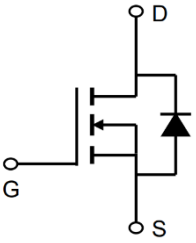
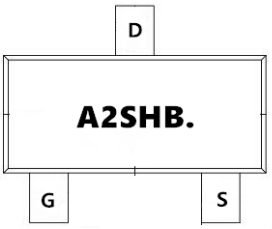
AP2302CI

20V N-Channel Enhancement Mode MOSFET

Description

The AP2302CI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.





General Features

V_{DS} = 20V I_D =2.3A

$R_{DS(ON)}$ < 52mΩ@ V_{GS}=4.5V

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP2302CI	SOT-23	A2SHB.	3000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter		Limit	Unit
V_{DS}	Drain-source Voltage		20	V
V_{GS}	Gate-source Voltage		±12	V
I_D	Drain Current	T_A=25℃ @ Steady State	2.3	A
		T_A=70℃ @ Steady State	1.8	
IDM	Pulsed Drain Current [A]		14	A
P_D	Total Power Dissipation @ T_A=25℃		0.7	W
$R_{\theta}JA$	Thermal Resistance Junction-to-Ambient@Steady State		178	℃/ W
TJ ,TSTG	Junction and Storage Temperature Range		-55～+150	℃

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Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}= 0V, I_D=250μA	20	21		V
IDSS	Zero Gate Voltage Drain Current	V_{DS}=20V,V_{GS}=0V,T_C=25℃			1	μA
IGSS	Gate-Body Leakage Current	V_{GS}= ±12V, V_{DS}=0V			±100	nA
VGS(th)	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D=250μA	0.45	0.58	0.9	V
RDS(ON)	Static Drain-Source On-Resistance	V_{GS}= 4.5V, I_D=3.0A		48	52	mΩ
		V_{GS}= 2.5V, I_D=2.0A		55	66	
C_{iss}	Input Capacitance	V_{DS}=10V,V_{GS}=0V,f=1MHZ		280		pF
C_{oss}	Output Capacitance			46		
C_{rss}	Reverse Transfer Capacitance			29		
Q_g	Total Gate Charge	V_{GS}=4.5V,V_{DS}=10V,I_D=3.0A		2.9		nC
Q_{gs}	Gate Source Charge			0.4		
Q_{gd}	Gate Drain Charge			0.6		
tD(on)	Turn-on Delay Time	V_{GS}=4.5V,V_{DD}=10V, R_L=1.5Ω, R_{GEN}=3Ω		13		ns
t_r	Turn-on Rise Time			54		
tD(off)	Turn-off Delay Time			18		
t_f	Turn-off Fall Time			11		
I_S	Maximum Body-Diode Continuous Current				3.0	A
V_{SD}	Diode Forward Voltage	I_S=3.0A,V_{GS}=0V			1.2	V

Note：

1、Pulse Test: Pulse Width≤300us,Duty cycle ≤2%.

2、Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

Typical Characteristics

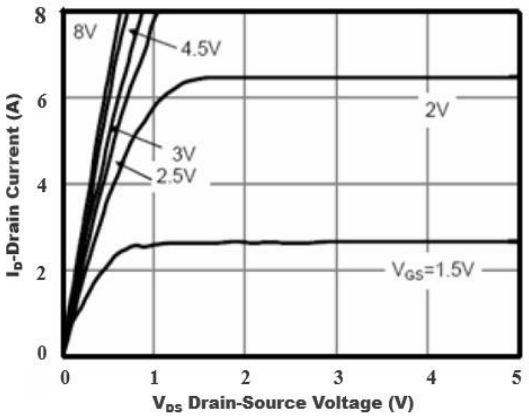


Figure1. Output Characteristics

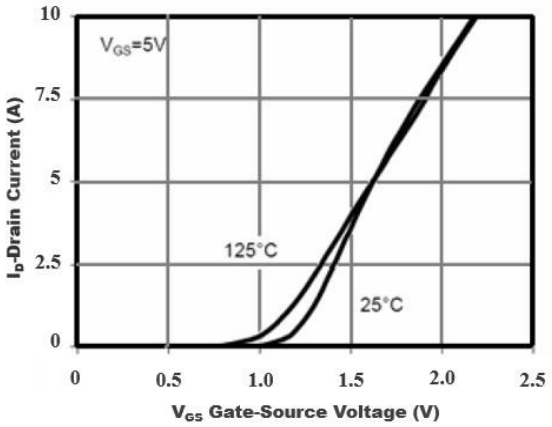


Figure2. Transfer Characteristics

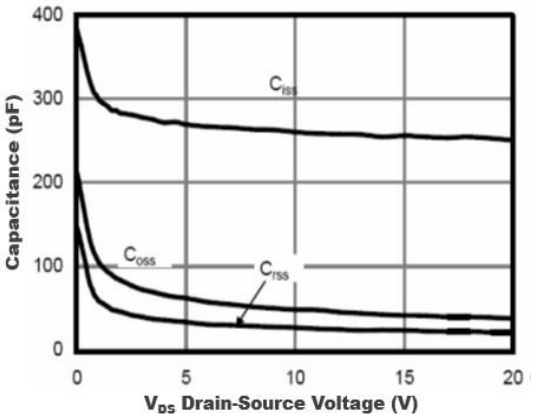


Figure3. Capacitance Characteristics

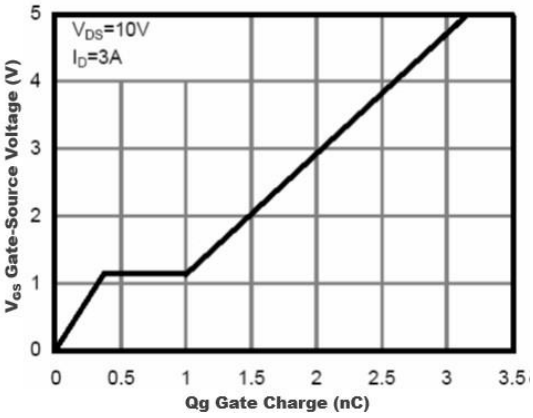


Figure4. Gate Charge

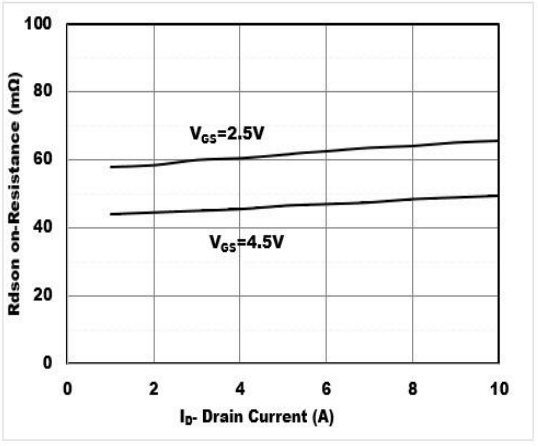


Figure5. Drain-Source on Resistance

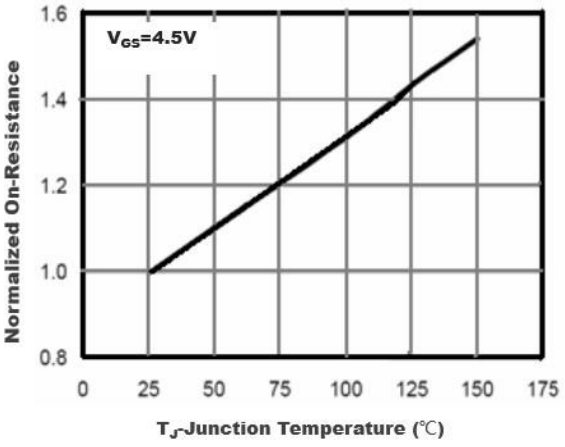


Figure6. Drain-Source on Resistance

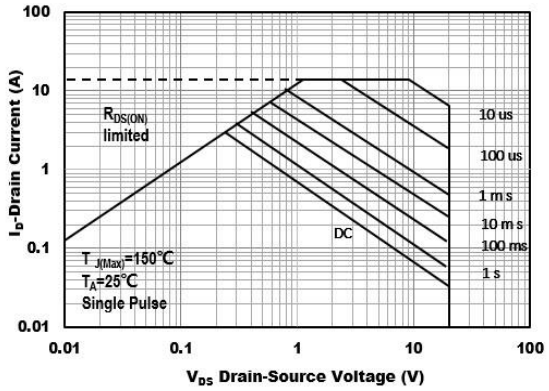


Figure7. Safe Operation Area

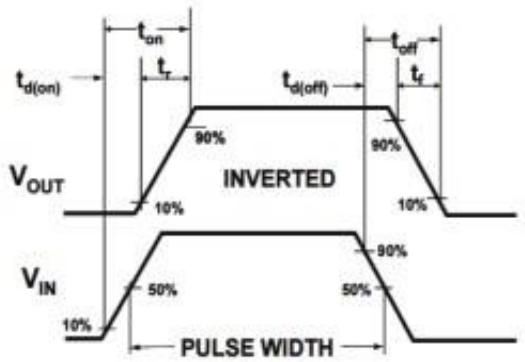
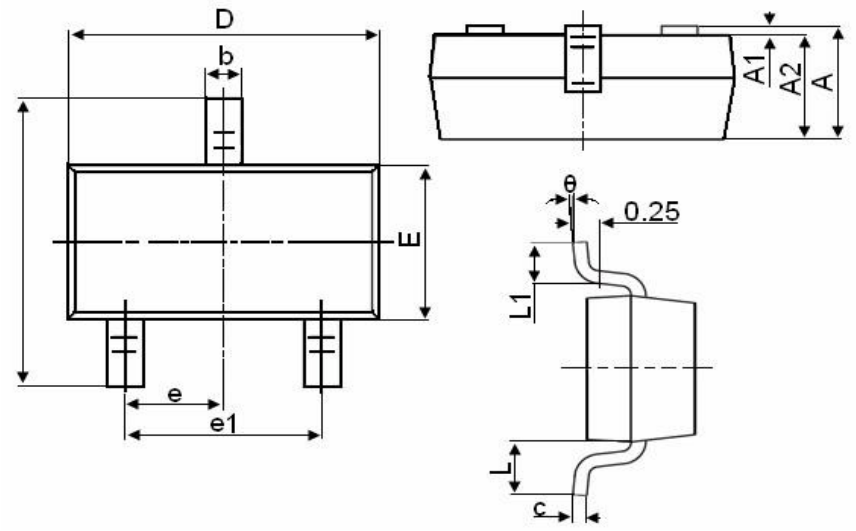


Figure8. Switching wave

Package Mechanical Data-SOT-23



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

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